

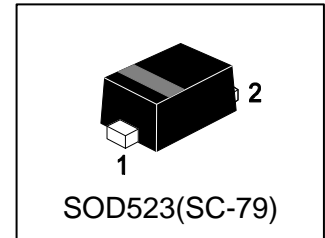
LRB521S-40T1G

S-LRB521S-40T1G

Schottky Barrier Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low VF.
- Silicon epitaxial planar
- Extremely small surface mounting type.



2. APPLICATIONS

- Low current rectification and high speed switching

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LRB521S-40T1G	S	3000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

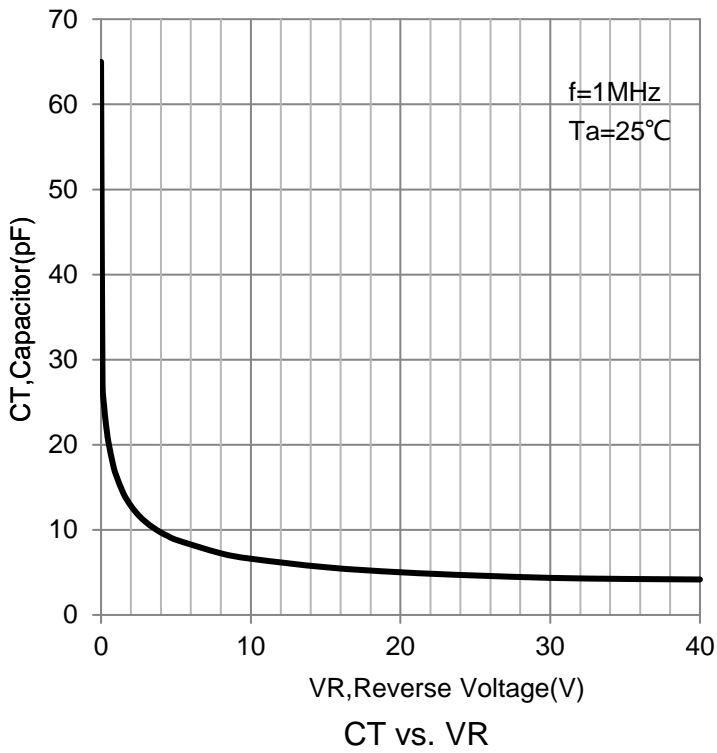
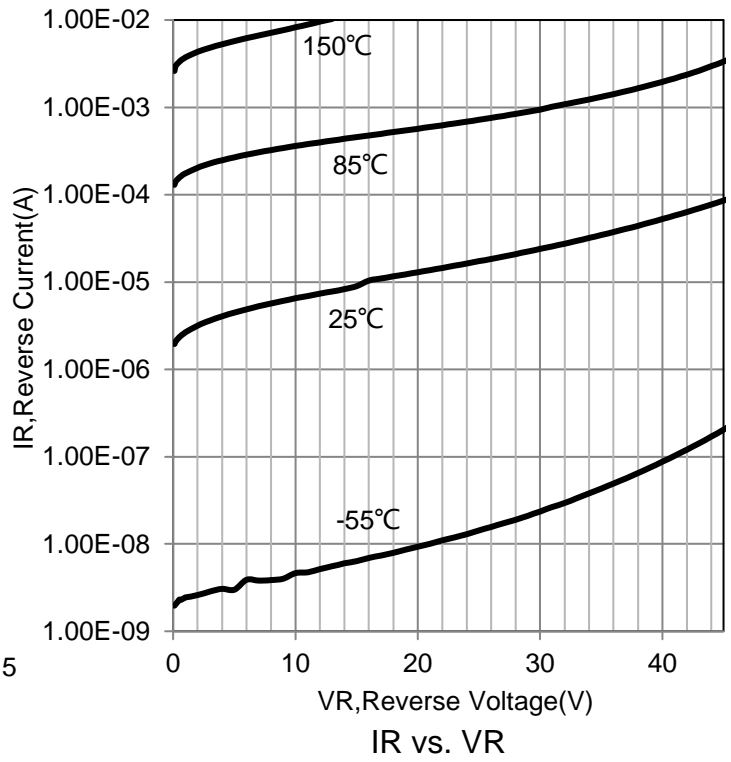
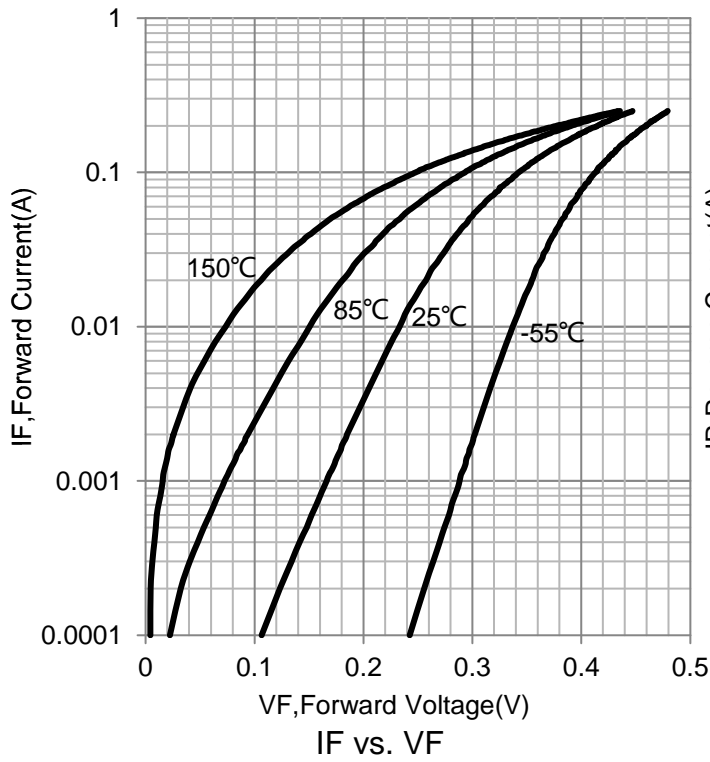
Parameter	Symbol	Limits	Unit
DC Reverse Voltage	VR	40	V
Mean Rectifying Current	IO	200	mA
Peak Forward Surge Current(Note 1)	IFSM	4	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55~+125	°C

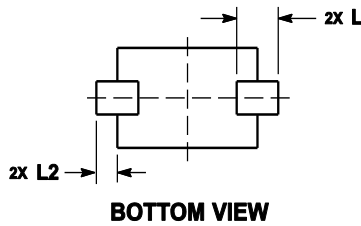
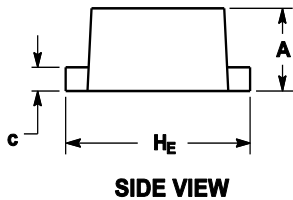
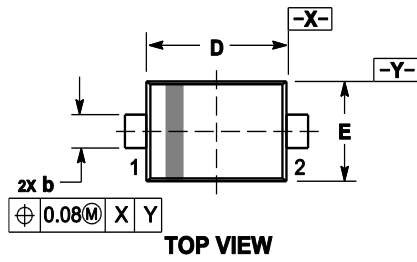
1.60Hz for 1[∞]

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Max.	Unit
Forward voltage (IF =10mA)	VF	0.16	0.3	V
(IF =100mA)		0.31	0.45	
(IF =200mA)		0.37	0.52	
Reverse Current (VR=10V)	IR	-	20	μA
(VR=40V)		-	90	
ESD breakdown voltage (C=100pF,R=1.5Kohm forward and reverse 1 time)	ESD	8	-	KV

6.ELECTRICAL CHARACTERISTICS CURVES

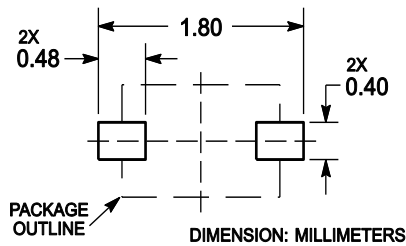


7. OUTLINE AND DIMENSIONS


Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.60	0.70	0.020	0.024	0.028
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.07	0.14	0.20	0.003	0.006	0.008
D	1.10	1.20	1.30	0.043	0.047	0.051
E	0.70	0.80	0.90	0.028	0.031	0.035
H _E	1.50	1.60	1.70	0.059	0.063	0.067
L	0.30 REF			0.012 REF		
L ₂	0.15	0.20	0.25	0.006	0.008	0.010

8. SOLDERING FOOTPRINT


单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)

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